BD809 (NPN), BD810 (PNP)

Plastic High Power Silicon Transistors

These devices are designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.

Features

- High DC Current Gain
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	80	Vdc
Collector−Base Voltage	V_{CBO}	80	Vdc
Emitter−Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	10	Adc
Base Current	I_B	6.0	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 90 0.72	 W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	1.39	°C/W

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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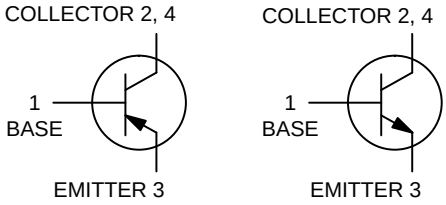
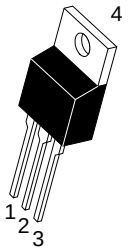
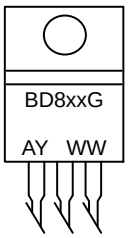
10 AMPERE POWER TRANSISTORS 80 VOLTS 90 WATTS





TO−220
CASE 221A
STYLE 1

MARKING DIAGRAM



BD8xx	=	Device Code x = 09 or 10
A	=	Assembly Location
Y	=	Year
WW	=	Work Week
G	=	Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
BD809G	TO−220 (Pb−Free)	50 Units/Rail
BD810G	TO−220 (Pb−Free)	50 Units/Rail

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector−Emitter Sustaining Voltage (Note 1) (I_C = 0.1 Adc, I_B = 0)	BV_{CEO}	80	–	Vdc
Collector Cutoff Current (V_{CB} = 80 Vdc, I_E = 0)	I_{CBO}	–	1.0	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	–	2.0	mAdc
DC Current Gain (I_C = 2.0 A, V_{CE} = 2.0 V) (I_C = 4.0 A, V_{CE} = 2.0 V)	h_{FE}	30 15	– –	–
Collector−Emitter Saturation Voltage (Note 1) (I_C = 3.0 Adc, I_B = 0.3 Adc)	$V_{CE(sat)}$	–	1.1	Vdc
Base−Emitter On Voltage (Note 1) (I_C = 4.0 Adc, V_{CE} = 2.0 Vdc)	$V_{BE(on)}$	–	1.6	Vdc
Current−Gain Bandwidth Product (I_C = 1.0 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	1.5	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

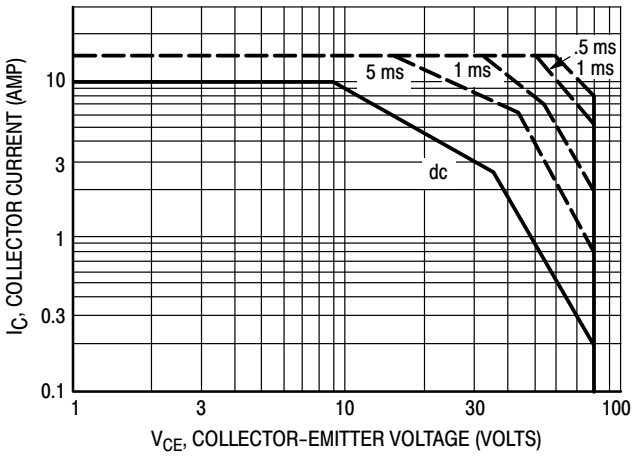


Figure 1. Active Region DC Safe Operating Area

(see Note on page 3)

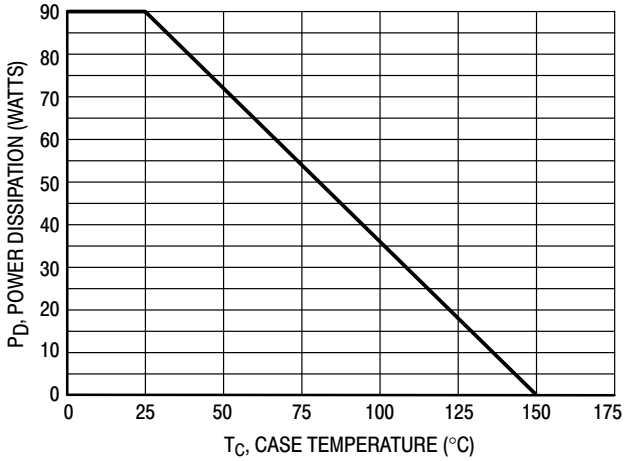


Figure 2. Power−Temperature Derating Curve

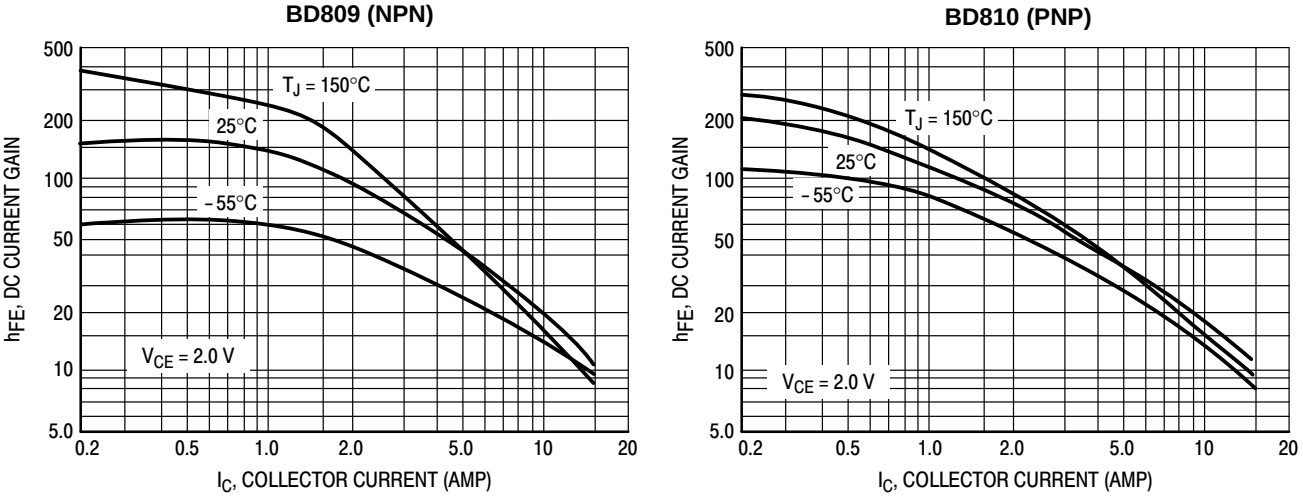


Figure 3. DC Current Gain

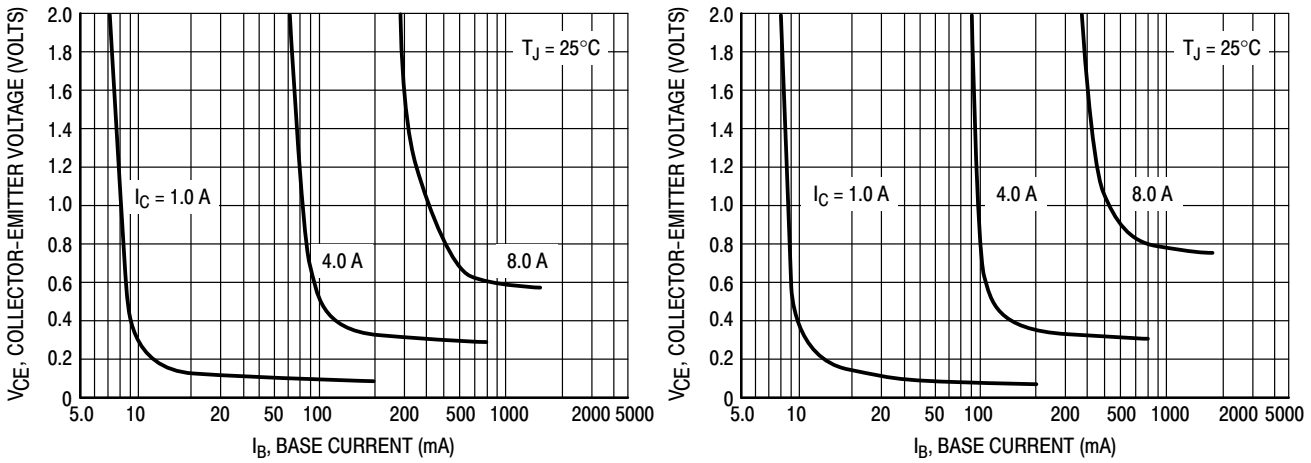


Figure 4. Collector Saturation Region

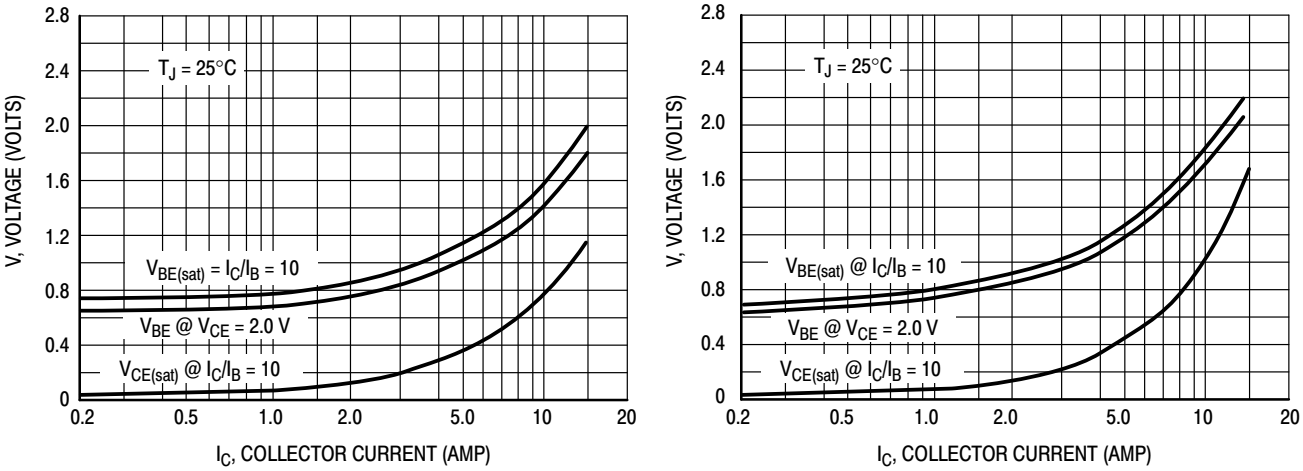


Figure 5. "On" Voltages

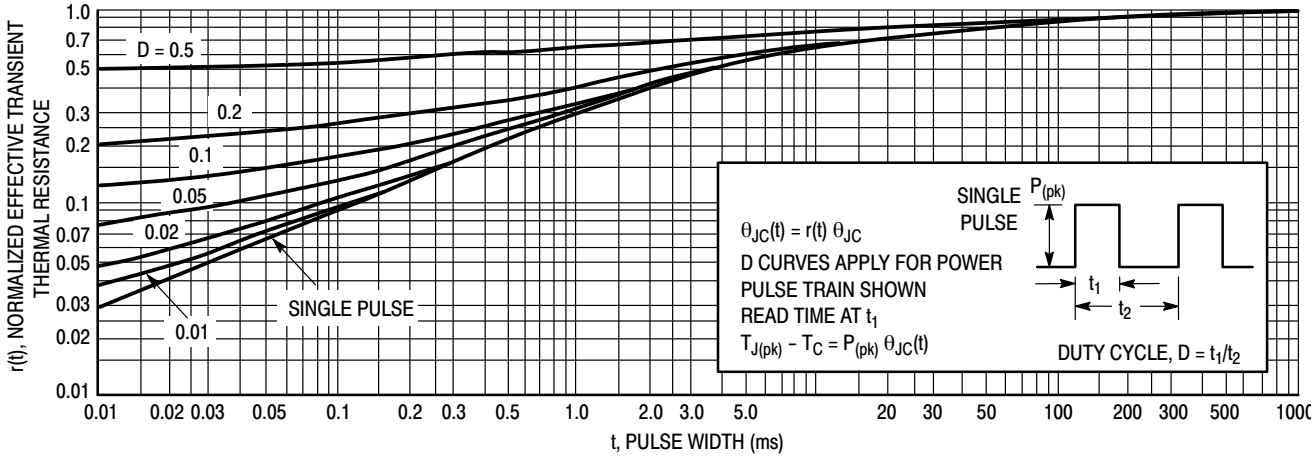


Figure 6. Thermal Response

Note:

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

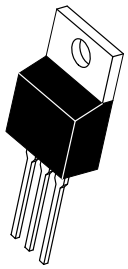
The data of Figure 1 is based on $T_{J(pk)}$ = 150°C; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

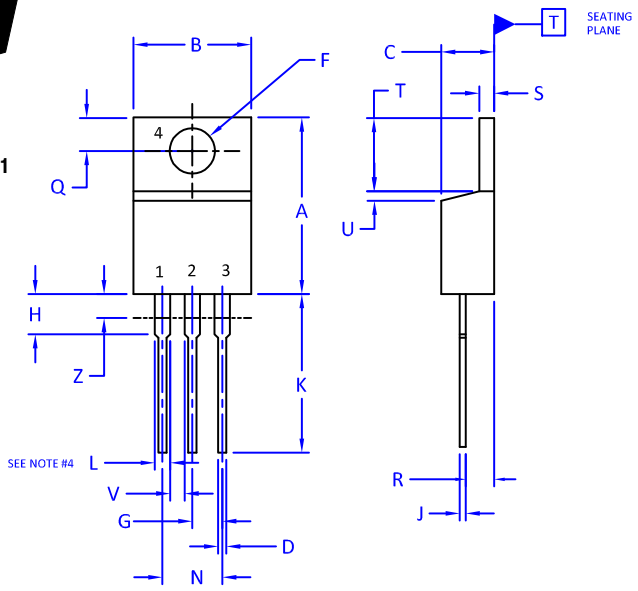
ON Semiconductor®

TO−220
CASE 221A−09
ISSUE AJ

DATE 05 NOV 2019



SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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DESCRIPTION:	**TO−220**	**PAGE 1 OF 1**